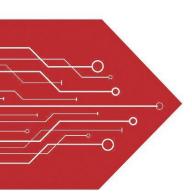
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data speet





FEATURES

- → The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction

- Low power loss, high efficiency
 Built-in strain relief, ideal for automated placement
 High forward surge current capability
 High temperature soldering guaranteed: 250°C/10 seconds at terminals



MECHANICAL DATA

Case: JEDEC DO-214AC molded plastic body **Terminals**: leads solderable per MIL-STD-750, Method 2026 Polarity: Color band denotes cathode end Mounting Position: Any Weight: 0.003 ounce, 0.093 grams 0.004 ounce, 0.111 grams SMA(H)



SMA

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	SS12	SS13	SS14	SS15	SS16	SS18	SS110	UNITS
Maximum repetitive peak reverse voltage	VRRM	20	30	40	50	60	80	100	VOLTS
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	VOLTS
Maximum DC blocking voltage	VDC	20	30	40	50	60	80	100	VOLTS
Maximum average forward rectified current at TL(see fig.1)	l(AV)	v) 1.0			Amp				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	Іғѕм	40.0		Amps					
Maximum instantaneous forward voltage at 1.0A	VF	0.45 0.55 0.70 0.8		0.8	5	Volts			
Maximum DC reverse current TA=25℃ at rated DC blocking voltage TA=100℃	IR	0.5		mA					
Typical junction capacitance (NOTE 1)	Cı	110 90			pF				
Typical thermal resistance (NOTE 2)	RqJA	88.0			°C/W				
Operating junction temperature range	TJ,	-65 to +125 -65 to +150			DС				
Storage temperature range	Тѕтс	-65 to +150			°C				

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C. 2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas





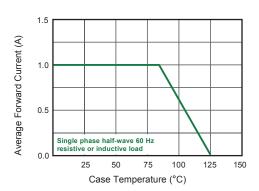


Fig.3 Typical Forward Characteristic

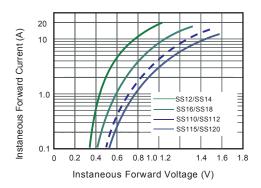


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

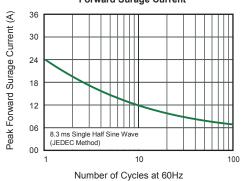


Fig.2 Typical Reverse Characteristics

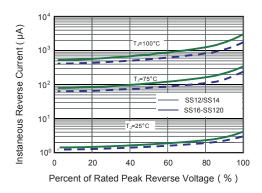


Fig.4 Typical Junction Capacitance

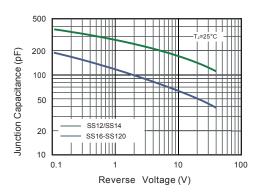
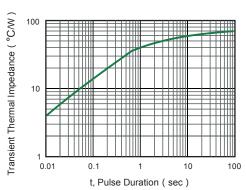
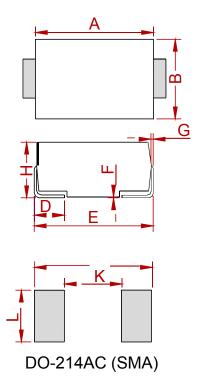


Fig.6- Typical Transient Thermal Impedance





PACKAGE MECHANICAL DATA



	Dimensions						
Ref.	Millin	neters	Inches				
	Min.	Max.	Min.	Max.			
Α	4.25	4.65	0.167	0.183			
В	2.50	2.90	0.098	0.114			
С	1.35	1.65	0.053	0.065			
D	0.76	1.52	0.030	0.060			
Е	4.93	5.28	0.194	0.208			
F	0.051	0.203	0.002	0.008			
G	0.15	0.31	0.006	0.012			
Н	1.98	2.41	0.078	0.095			
J	6.50		0.256				
K		2.30		0.090			
L	1.70		0.067				

REEL SPECIFICATION

P/N	PKG	QTY
SS12-MS/SS110-MS	SMA	2000



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Compiance

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